

**FEATURES**

High voltage and high current  
 Excellent hFE Linearity  
 Low noise ,Complementary to C1815



**A1015 (PNP)**



MARKING: BA

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current -Continuous	I <sub>C</sub>	0.15	A
Collector Power Dissipation	P <sub>C</sub>	0.2	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -100u A, I <sub>E</sub> =0	-50			V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -0.1mA, I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100 u A, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CB</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.1	u A
Collector cut-off current	I <sub>CE</sub>	V <sub>CE</sub> = -50V, I <sub>B</sub> =0			-0.1	u A
Emitter cut-off current	I <sub>EB</sub>	V <sub>EB</sub> =- 5V, I <sub>C</sub> =0			-0.1	u A
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> = -2mA	130		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100 mA, I <sub>B</sub> = -10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100 mA, I <sub>B</sub> = -10mA			-1.1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> = -1mA f=30MHz	80			MHz

CLASSIFICATION OF h<sub>FE</sub>

Rank	L	H
Range	130-200	200-400

**A1015** Typical Characteristics

